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Selectivity of Ti-doped In₂O₃ ceramics as an ammonia sensor

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Abstract

Nanoscale In_2O_3 powders doped with titanium were prepared by using $InCl_3 \cdot 4H_2O$ as a source matter. The materials doped with Ti⁴⁺ ions obviously showed the enhanced selectivity to ammonia sensor, compared with two reducing gases of H_2 and CO, in the concentration range of 5–1000 ppm at a low operating current (165 mA, equal to 145 °C). Characterization of the materials was performed by thermal analysis, XRD, BET, FTIR, and magnetic susceptibility measurement. The mechanism of the selective gas sensing is proposed on the basis of the differences in gas molecular structure for adsorption and activation.

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Keywords: In2O3; Ammonia sensor; Selectivity; Sensing mechanism

1. Introduction

An efficient gas sensor must have high sensitivity and good selectivity at low operating temperature. Because of the complexity of gas sensing mechanism, the main method of giving suitable selectivity is implemented generally by altering the operating temperature, using effective gas filters, and adding catalytically active dopants at present [1,2].

Ammonia (NH₃) is a colorless gas with a special odour and is very harmful to the human body. It is not only used largely to synthesize various materials in chemical industries, but also may exist in agricultural production and our dwelling place. Therefore, it is necessary to monitor the concentration of ammonia for atmospheric environment measurement and control. In_2O_3 can be used as a material of ammonia sensors, but the major problem associated with In_2O_3 is its crosssensitivity, as encountered with most oxide semiconductor sensors. As NH₃, H₂ and CO are all reducing gases, conventional ammonia sensors are invariably more sensitive to H₂

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and CO than to NH₃ [3]. The literature reported that the main cause of the low sensitivity to NH3 is the competitive occurrence of two reactions during the NH₃ oxidation on the sensor surface; consumption of chemisorbed oxygen and chemisorption of negatively charged NO_x species (especially NO_2) as the oxidation products of NH₃ [4]. A sensitization mechanism has been proposed which explains the sensitivity of NH3, H2 and CO of metal oxide sensors, and it is known that a Pt-catalyst can greatly increase the sensor response [5–7]. With respect to the oxidation reactions, the adsorbed O_{2ads}⁻ and O_{ads}⁻ species and also the exposed oxygen atoms on step sites are classified as reactants [8,9]. The details are well described by Yamazoe et al. [10] and Kohl [11] about the surface reactions between metal oxides and oxygen adsorbates. Romanovskaya [12] reported that Pt-loaded In₂O₃ ceramics can increase the sensitivity to NH₃. However, there is little related description about how to decrease the sensitivity to H₂ and CO for this kind of materials. In this paper, therefore, Ti⁴⁺-doped In₂O₃ materials are examined for detecting NH₃, and it is found that the materials exhibit significantly larger responses to NH₃ than to H₂ and CO. The mechanism for the selective NH₃ detection is also explained on the basis of the differences in molecular structure for adsorption and activation.

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2. Experimental

2.1. Preparation of specimens

Pure and Ti⁴⁺-doped In₂O₃ nano-particles were obtained by using indium chloride (InCl₃·4H₂O) and tetrabutyl titanate (Ti(C₄H₉O)₄) as starting materials and polyethylene glycol 2000 as a dispersant, and an ammonia water solution was joined for preparing the indium hydroxide sol. The amount of the doped Ti⁴⁺ was 0.5, 1.0 or 5.0 mol%. To achieve the homogeneous sol, the sol was stabilized with nitric acid and mixed around for several days. After vacuum-drying at 80 °C, the powder obtained (precursor) was made into thick films.

The measurement electrode was composed of a pair of four-fingered gold electrodes of 120 μ m width and 40 μ m spacing between fingers on an alumina substrate. The overlap distance of the fingers was 400 μ m, and a Ni–Cr heater (37 Ω) was made on the opposing face of the substrate. The thick film was coated with a layer of sensor materials of ~10 μ m thick mixed with terpineol (chemical pure grade), followed by vacuum-drying at 80 °C. Then, the thick films were annealed at different temperatures for 1 h under ambient pressure. Finally the sensors were subjected to measurement of sensor responses to NH₃, H₂ and CO.

2.2. Characterization

The thermal effects associated with the heat treatment of uncalcined powders were investigated with an instrument of thermogravimetry and differential scanning calorimentry (TG and DSC, NETZSCH STA 449, Germany) at a rate of $10 \,^{\circ}\text{C}\,\text{min}^{-1}$ in flowing nitrogen from room temperature to $1000 \,^{\circ}\text{C}$. Specific surface areas were measured by a BET method with a nitrogen adsorption apparatus (Model: ASAP 2000, Micromeritics Instrument Group, USA). Crystalline structure of the samples was analyzed by powder X-ray diffraction (XRD, Model: X'pert, Philips Corp., Holland), and crystallite size was calculated according to the wellknown Scherrer's equation.

FTIR spectra of the annealed powders were recorded by a KBr method using a Spectrum-2000 FTIR spectrophotometer (Perkin-Elmer, USA) in the range of 400–4000 cm⁻¹. The surface structure of the thick film sensors was investigated by environmental scanning electron microscopy (ESEM, XL30, Philips Corp.). Magnetic susceptibility (χ) was measured by D-200 Research Magnetic Faraday Balance (Cahn Instrument Ltd., USA) with a sensitivity of 0.0001 mg at room temperature (25 °C) under high vacuum (10⁻⁶ Torr).

The materials were made into thick films for measuring the sensor responses to NH_3 , H_2 and CO. The resistance of a sensitive element was measured in air (Ra) and in air-gas mixtures (Rg) under the same operating current. The gas response magnitude (S) was defined as the ratio of Ra to Rg (S=Ra/Rg). The concentration of NH_3 , H_2 and CO were 5–1000 ppm in air.

3. Results and discussion

3.1. Analysis and measurement

The TG curve of the precursor (pure In_2O_3) showed two apparent weight loss stages (Fig. 1). The first weight loss near 100 °C is mainly due to the loss of water, while second at 100-320 °C is associated with burning of the residual dispersant, removal of OH⁻ group and decomposition of HNO₃. The DSC curve indicates two endothermic peaks near 100 and 240 °C, and an exothermic peaks at 310 °C. Two weight loss stages are observed corresponding to the two endothermic peaks. The exothermic peak at 310 °C is due to the buring of the residual dipersant. Therefore, the calcination temperatures higher than 350 °C were chosen in present experiments. As the result, the largest response to 1000 ppm NH₃ of the pure In₂O₃ sensor was achieved at 550 °C among the calcination temperatures of 350-850 °C (Fig. 2). Therefore, the effects of Ti4+ -doping on the gas-sensing characteristics of In₂O₃ sensors were examined at this particular calcination temperature (550 °C).

Fig. 3 shows the XRD patterns of pure and Ti^{4+} -doped In_2O_3 samples calcined at 550 °C for 1 h. The XRD patterns with the largest peak intensity of crystal plane 222 indicate the main crystal phase of bixbyite-type structure (cubic-In₂O₃, space group Ia3; the unit cell contains 16 formulae). No impure phases corresponding to titanium compounds were



Fig. 1. TG, DTG and DSC curves of pure In_2O_3 .



Fig. 2. Annealing temperature dependence of sensor response (Rg/Ra) to 1000 ppm NH_3 of pure In₂O₃.

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